



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Ι _D T _A = +25°C
60V	80mΩ @ V _{GS} =10V	3.5A
000	150mΩ @ V _{GS} =4.5V	2.5A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

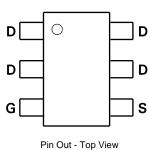
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

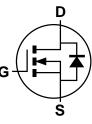
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.018 grams (Approximate)



Top View





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
ZXMN6A08E6TA	Standard	SOT26	3,000 / Tape & Reel
ZXMN6A08E6TC	Standard	SOT26	10,000 / Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT26							
6		ΥM					
 П							

 $\begin{array}{l} 6A8 = Product Type Marking Code \\ YM = Date Code Marking \\ Y \ or \ \overline{Y} = Year \ (ex: C = 2015) \\ M \ or \ \overline{M} = Month \ (ex: 9 = September) \end{array}$

Date Code Key

Notes:

Date Code Key												
Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
WOITUT	Jan	160	IVIAI	лμ	Iviay	Juli	Jui	Aug	Jep	001	NOV	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

(Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GS}	±20	V
		(Note 6)		3.5	
Continuous Drain Current	$V_{GS} = 10V$	T _A = +70°C (Note 6)	ID	2.8	А
		(Note 5)		2.8	
Pulsed Drain Current	$V_{GS}=10V$	(Note 7)	I _{DM}	16	А
Continuous Source Current (Body Diode) (Note 6)		(Note 6)	Is	2.6	А
Pulsed Source Current (Bod	y Diode)	(Note 7)	I _{SM}	16	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)		1.1 8.8	W
Linear Derating Factor	(Note 6)	PD	1.7 13.6	mW/°C
	(Note 5)		113	2011/
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	73	°C/W
Operating and Storage Temperature Range		TJ, T _{STG}	-55 to +150	°C

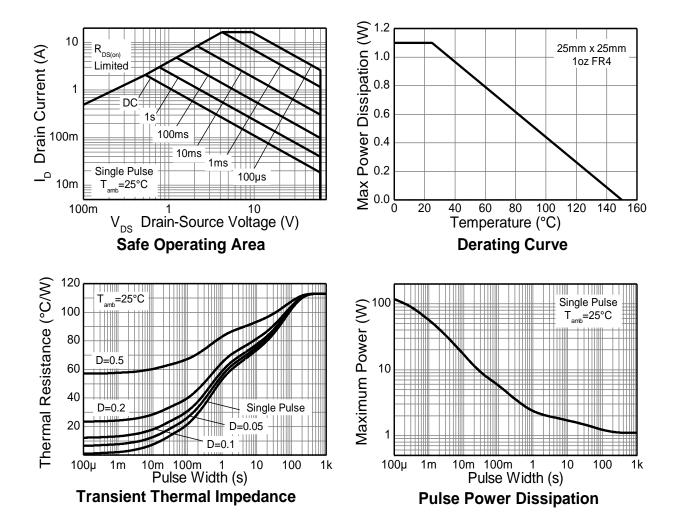
Notes: 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as Note 5, except the device is measured at t \leq 10 sec.

7. Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.



Thermal Characteristics





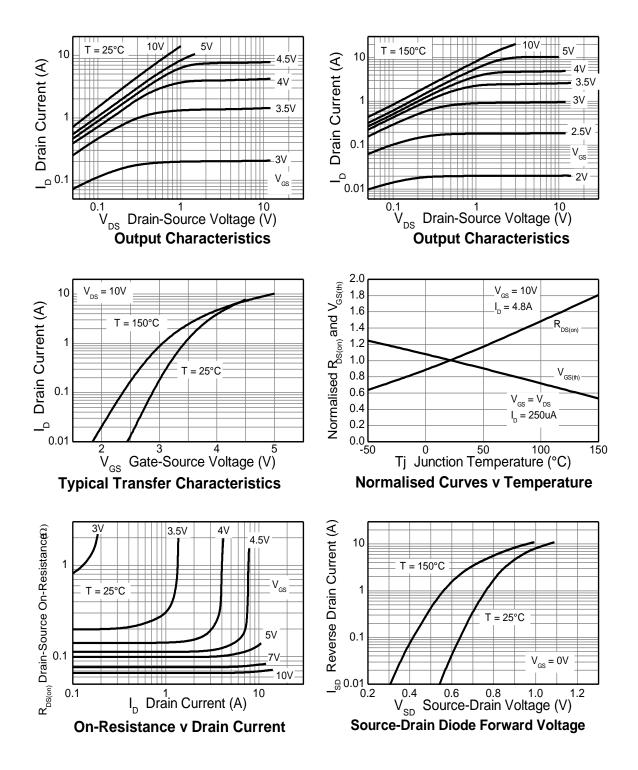
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS						•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	—		V	$I_{D} = 250 \mu A, V_{C}$	₆₅ = 0V
Zero Gate Voltage Drain Current	I _{DSS}	_	—	0.5	μA	$V_{DS} = 60V, V_{G}$	s = 0V
Gate-Source Leakage	IGSS	_	—	±100	nA	V _{GS} = ±20V, V	DS = 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0	_	_	V	$I_{D} = 250 \mu A, V_{D}$	$v_{\rm S} = V_{\rm GS}$
Statia Drain Source On Begistenes (Note 8)	Denne		0.067	0.080	Ω	V_{GS} = 10V, I_D	= 4.8A
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}		0.100	0.150	12	V _{GS} = 4.5V, I _D = 4.2A	
Forward Transconductance (Notes 8 & 9)	g _{fs}		6.6		S	$V_{DS} = 15V, I_D =$	= 4.8A
Diode Forward Voltage (Note 8)	V _{SD}	_	0.88	1.2	V	I _S = 4A, V _{GS} = 0V, T _J = +25°C	
Reverse Recovery Time (Note 9)	t _{rr}	_	19.2	_	ns	I _F = 1.4A, di/dt = 100A/μs,	
Reverse Recovery Charge (Note 9)	Qrr	_	30.3	_	nC	T _J = +25°C	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		459	—	pF		0) (
Output Capacitance	Coss		44.2		pF	V _{DS} = 40V, V _{GS} = 0V f = 1MHz	
Reverse Transfer Capacitance	Crss		24.1	_	pF		
Total Gate Charge (Note 10)	Qg	_	3.7	_	nC	$V_{GS} = 4.5V$	
Total Gate Charge (Note 10)	Qg	_	5.8	_	nC		V _{DS} = 30V
Gate-Source Charge (Note 10)	Q _{gs}	_	1.4	_	nC	$V_{GS} = 10V$	$I_D = 1.4A$
Gate-Drain Charge (Note 10)	Q _{gd}		1.9		nC		
Turn-On Delay Time (Note 10)	t _{D(on)}	_	2.6		ns		
Turn-On Rise Time (Note 10)	tr		2.1		ns	V _{DD} = 30V, V _G	s = 10V
Turn-Off Delay Time (Note 10)	t _{D(off)}		12.3		ns	I _D = 1.5A, R _G ≘	6.0Ω
Turn-Off Fall Time (Note 10)	t _f		4.6		ns	7	

 8. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
9. For design aid only, not subject to production testing.
10. Switching characteristics are independent of operating junction temperatures. Notes:

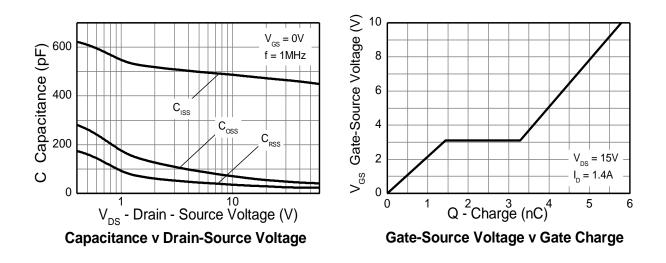


Typical Characteristics

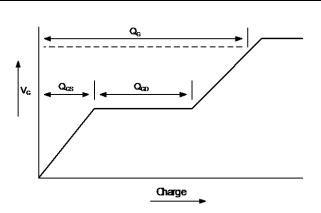




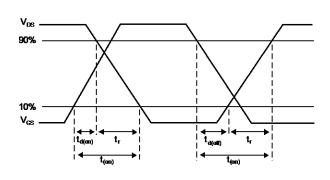
Typical Characteristics (cont.)



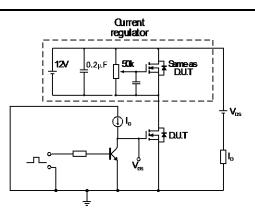
Test Circuits



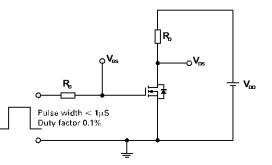




Switching time waveforms



Gate charge test circuit

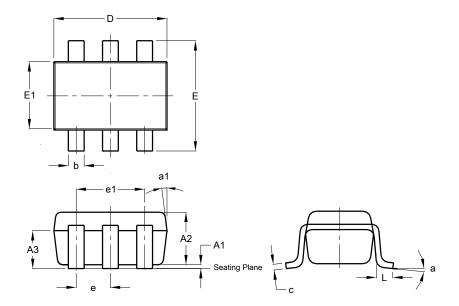


Switching time test circuit



Package Outline Dimensions

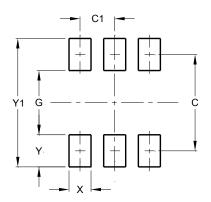
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT26								
Dim	Min	Max	Тур						
A1	0.013	0.10	0.05						
A2	1.00	1.30	1.10						
A3	0.70	0.80	0.75						
b	0.35	0.50	0.38						
С	0.10	0.20	0.15						
D	2.90	3.10	3.00						
е	-	-	0.95						
e1	-	-	1.90						
E	2.70	3.00	2.80						
E1	1.50	1.70	1.60						
L	0.35	0.55	0.40						
а	-	-	8°						
a1	-	-	7°						
All	Dimen	sions	in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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